L Number	Hits	Search Text	DB	Time stamp
-	16216	etch\$3 with ((Si silicon poly poly-Si	USPAT;	2004/03/07 23:39
		polysilicon a-Si silicone) and (plasma vapor	US-PGPUB;	
		dry gas\$5) and (rate per \$3/s \$3/sec \$3/min	EPO; JPO; DERWENT;	
		\$3/minute \$3/h \$3/hr \$3/hour))	IBM TDB	
_	3482	etch\$3 with ((Si silicon poly poly-Si	USPAT;	2004/03/07 21:34
	3402	polysilicon a-Si silicone) with (plasma	US-PGPUB;	
	-	vapor dry gas\$5) with (rate per \$3/s \$3/sec	EPO; JPO;	
		\$3/min \$3/minute \$3/h \$3/hr \$3/hour))	DERWENT;	
			IBM_TDB	
-	5720		USPAT;	2004/03/07 21:36
		polysilicon a-Si silicone) and etch\$3 near	US-PGPUB;	
		(plasma vapor dry gas\$5) and etch\$3 near	EPO; JPO; DERWENT;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)	IBM TDB	
_	953		USPAT;	2004/03/07 22:35
_	223	polysilicon a-Si silicone) same etch\$3 near	US-PGPUB;	
		(plasma vapor dry gas\$5) same etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)	IBMTDB	
-	217		USPAT;	2004/03/07 21:39
		polysilicon a-Si silicone) with etch\$3 near	US-PGPUB;	
		(plasma vapor dry gas\$5) with etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
	Ω	\$3/hr \$3/hour) etch\$3 adj (Si silicon poly poly-Si	USPAT;	2004/03/07 21:49
_	0	polysilicon a-Si silicone) near etch\$3 near	US-PGPUB;	
		(plasma vapor dry gas\$5) with etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)	IBM_TDB	
-	1830		USPAT;	2004/03/07 21:54
		polysilicon a-Si silicone) and (plasma vapor	US-PGPUB;	
		dry gas\$5) and (rate per \$3/s \$3/sec \$3/min	EPO; JPO;	
		\$3/minute \$3/h \$3/hr \$3/hour))) and PECVD	DERWENT; IBM TDB	
_	664	(etch\$3 near (Si silicon poly poly-Si	USPAT;	2004/03/07 21:49
	004	polysilicon a-Si silicone) and etch\$3 near	US-PGPUB;	
		(plasma vapor dry gas\$5) and etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)) and PECVD	IBM_TDB	
-	378		USPAT;	2004/03/07 21:49
		polysilicon a-Si silicone) with (plasma	US-PGPUB;	
		vapor dry gas\$5) with (rate per \$3/s \$3/sec	EPO; JPO; DERWENT;	
		\$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and PECVD	IBM TDB	
	95	l	USPAT;	2004/03/07 21:49
	75	polysilicon a-Si silicone) same etch\$3 near	US-PGPUB;	, ,
#1		(plasma vapor dry gas\$5) same etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)) and PECVD	IBM_TDB	0004/00/00 05
-	16		USPAT;	2004/03/07 21:49
		polysilicon a-Si silicone) with etch\$3 near	US-PGPUB; EPO; JPO;	
		(plasma vapor dry gas\$5) with etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)) and PECVD	IBM TDB	
_	648		USPAT;	2004/03/07 22:59
		polysilicon a-Si silicone) and (plasma vapor	US-PGPUB;	
		dry gas\$5) and (rate per \$3/s \$3/sec \$3/min	EPO; JPO;	
		\$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si	DERWENT;	
		amor-Si amorph-Si amorphous-Si	IBM_TDB	
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
		amor adj Silicon amorph adj Silicon		
	240	amorphous adj Si)	USPAT;	2004/03/07 21:58
-	249	(etch\$3 near (Si silicon poly poly-Si polysilicon a-Si silicone) and etch\$3 near	US-PGPUB;	2004/05/07/21.50
		(plasma vapor dry gas\$5) and etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si	IBM_TDB	
			_	1
1111		amorphous-Si "Si.sub.amorph" "Si.sub.am"		
		"Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)		

_	122	(etch\$3 with ((Si silicon poly poly-Si	USPAT;	2004/03/07 21:58
		polysilicon a-Si silicone) with (plasma	US-PGPUB;	
		vapor dry gas\$5) with (rate per \$3/s \$3/sec	EPO; JPO; DERWENT;	
		\$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si amor-Si amorph-Si amorphous-Si	IBM TDB	
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"	12155	
		amor adj Silicon amorph adj Silicon		
		amorphous adj Si)		
_	35	(etch\$3 adj (Si silicon poly poly-Si	USPAT;	2004/03/07 21:58
		polysilicon a-Si silicone) same etch\$3 near	US-PGPUB;	
		(plasma vapor dry gas\$5) same etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si	IBM_TDB	
		amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj		
		Silicon amorphous adj Si)		
	9	(etch\$3 adj (Si silicon poly poly-Si	USPAT;	2004/03/07 22:13
		polysilicon a-Si silicone) with etch\$3 near	US-PGPUB;	
		(plasma vapor dry gas\$5) with etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si	IBM_TDB	·
		amorphous-Si "Si.sub.amorph" "Si.sub.am"		
		"Si.sub.amor" amor adj Silicon amorph adj		-
		Silicon amorphous adj Si)	IIODAT.	2004/03/07 22:13
_	72	((etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor	USPAT; US-PGPUB;	2004/03/01 22:13
		dry gas\$5) and (rate per \$3/s \$3/sec \$3/min	EPO; JPO;	
		\$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si	DERWENT;	
		amor-Si amorph-Si amorphous-Si	IBM TDB	
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"	_	
		amor adj Silicon amorph adj Silicon		
	·	amorphous adj Si)) and etch\$3 near (a-Si		
		amor-Si amorph-Si amorphous-Si		
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
		amor adj Silicon amorph adj Silicon		
	5.6	amorphous adj Si) ((etch\$3 near (Si silicon poly poly-Si	USPAT;	2004/03/07 22:14
_	56	polysilicon a-Si silicone) and etch\$3 near	US-PGPUB;	2001,03,0, 22:11
		(plasma vapor dry gas\$5) and etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si	IBM_TDB	
		amorphous-Si "Si.sub.amorph" "Si.sub.am"		
		"Si.sub.amor" amor adj Silicon amorph adj		
		Silicon amorphous adj Si)) and etch\$3 near		
		(a-Si amor-Si amorph-Si amorphous-Si		
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
		amor adj Silicon amorph adj Silicon		
	16	amorphous adj Si) ((etch\$3 with ((Si silicon poly poly-Si	USPAT;	2004/03/07 22:14
		polysilicon a-Si silicone) with (plasma	US-PGPUB;	
		vapor dry gas\$5) with (rate per \$3/s \$3/sec	EPO; JPO;	,
		\$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and	DERWENT;	
		(a-Si amor-Si amorph-Si amorphous-Si	IBM_TDB	
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
		amor adj Silicon amorph adj Silicon		
		amorphous adj Si)) and etch\$3 near (a-Si		
		amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
		amor adj Silicon amorph adj Silicon		
		amorphous adj Si)		
_	0		USPAT;	2004/03/07 22:14
		polysilicon a-Si silicone) with etch\$3 near	US-PGPUB;	
		(plasma vapor dry gas\$5) with etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si	IBM_TDB	
		amorphous-Si "Si.sub.amorph" "Si.sub.am"		
		"Si.sub.amor" amor adj Silicon amorph adj		
		Silicon amorphous adj Si)) and etch\$3 near (a-Si amor-Si amorph-Si amorphous-Si		
1		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
		amor adj Silicon amorph adj Silicon		
		amorphous adj Si)		
<u> </u>	<u> </u>			

_	7	((etch\$3 adj (Si silicon poly poly-Si	USPAT;	2004/03/07 22:21
		polysilicon a-Si silicone) same etch\$3 near	US-PGPUB;	
		(plasma vapor dry gas\$5) same etch\$3 near	EPO; JPO;	
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h	DERWENT;	
		\$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si	IBM_TDB	
		amorphous-Si "Si.sub.amorph" "Si.sub.am"		
		"Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)) and etch\$3 near		
		(a-Si amor-Si amorph-Si amorphous-Si		
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
		amor adj Silicon amorph adj Silicon		
		amorphous adj Si)		
_	1	("0633899").PN.	USPAT;	2004/03/07 22:22
	_		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(("0633899").PN.) and etch\$3 with rate	USPAT;	2004/03/07 22:24
			US-PGPUB;	
1			EPO; JPO;	
			DERWENT; IBM TDB	
	0	(/wocaseous) DN) and etch\$3 near (rate per	USPAT;	2004/03/07 22:25
-	0	(("0633899").PN.) and etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr	US-PGPUB;	
		\$3/\$ \$3/\$ec \$3/\limber	EPO; JPO;	
		\$37110d17	DERWENT;	
			IBM TDB	
_	10	(((etch\$3 with ((Si silicon poly poly-Si	USPAT;	2004/03/07 22:36
ļ		polysilicon a-Si silicone) with (plasma	US-PGPUB;	
		vapor dry gas\$5) with (rate per \$3/s \$3/sec	EPO; JPO;	
		\$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and	DERWENT;	
		(a-Si amor-Si amorph-Si amorphous-Si	IBM_TDB	
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
		amor adj Silicon amorph adj Silicon		
		amorphous adj Si)) and etch\$3 near (a-Si		
		amor-Si amorph-Si amorphous-Si		
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
		amor adj Silicon amorph adj Silicon amorphous adj Si)) not (((etch\$3 adj (Si		
		silicon poly poly-Si polysilicon a-Si		
		silicone) same etch\$3 near (plasma vapor dry		
		gas\$5) same etch\$3 near (rate per \$3/s		
		\$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))		
		and (a-Si amor-Si amorph-Si amorphous-Si		
7		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"	:	
		amor adj Silicon amorph adj Silicon	1	
		amorphous adj Si)) and etch\$3 near (a-Si		
		amor-Si amorph-Si amorphous-Si		
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon		•
		amor adj Silicon amorph adj Silicon amorphous adj Si))		
	118		USPAT;	2004/03/07 23:03
	110	polysilicon a-Si silicone) and (plasma vapor	US-PGPUB;	
		dry gas\$5) and (rate per \$3/s \$3/sec \$3/min	EPO; JPO;	
		\$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si	DERWENT;	
		amor-Si amorp-Si amorphous-Si	IBM_TDB	
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
		amor adj Silicon amorph adj Silicon		
		amorphous adj Si) with (H hydrogen)	IICD*	2004/02/07 22 23
_	21	(etch\$3 with ((Si silicon poly poly-Si	USPAT;	2004/03/07 23:04
		polysilicon a-Si silicone) and (plasma vapor	US-PGPUB; EPO; JPO;	
		dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si	DERWENT;	
		amor-Si amorp-Si amorphous-Si	IBM TDB	
		"Si.sub.amorph" "Si.sub.am" "Si.sub.amor"		
	-	amor adj Silicon amorph adj Silicon		
		amorphous adj Si) same ((H hydrogen) near	}	
		(percent\$3 content amount ratio atom\$3))		
<u> </u>		<u> </u>		

			<u>,</u>	
		<pre>(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si amor-Si amorp-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si) same ((H hydrogen) near (concentration percent\$3 content amount ratio atom\$3))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:34
-	4073	(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and etch\$3 near (preferential\$2 selective\$2 ratio) same (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:37
	2882		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:37
	608	l	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:38
	210		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:38
	140	((etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and etch\$3 near (preferential\$2 selective\$2 ratio) same (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")) and etch\$3 adj (preferential\$2 selective\$2 ratio) adj (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:38
_	82	(etch\$3 near (Si silicon poly poly-Si polysilicon a-Si silicone) and etch\$3 near (plasma vapor dry gas\$5) and etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and etch\$3 adj (preferential\$2 selective\$2 ratio) adj (oxide nitride SiO2 Si3N4 "SiO.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:40
_	44	"Si.sub.3 N.sub.4") (etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) with (plasma vapor dry gas\$5) with (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and etch\$3 adj (preferential\$2 selective\$2 ratio) adj (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:40

-	12	(etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) same etch\$3 near (plasma vapor dry gas\$5) same etch\$3 near	USPAT; US-PGPUB; EPO; JPO;	2004/03/07 23:40
		(rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and etch\$3 adj (preferential\$2 selective\$2 ratio) adj (oxide nitride SiO2 Si3N4 "SiO.sub.2"	DERWENT; IBM_TDB	
		"Si.sub.3 N.sub.4")		